HITACHI

ADE-208-156B(Z)

HRW26F
Silicon Schottky Barrier Diode for High Frequency Rectifying

HITACHI

Rev. 2
Nov. 1994

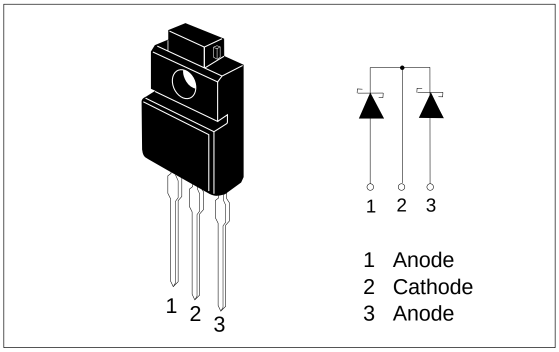
Features

- Low forward voltage drop. (V_F =0.55V max)
- High reverse voltage. (V_R =40V max)
- Full molded fin enables easy insulation from heat sink.

Ordering Information

Type No.	Laser Mark	Package Code
HRW26F	HRW26F	TO-220FM

Pin Arrangement



Absolute Maximum Ratings (Ta = 25°C) *

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	40	V
Average forward current	I_o**	10	A
Non-Repetitive peak forward surge current	I_{FSM}***	70	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40 to +125	°C

* Per one device

** Square wave, Duty (1/2), Tc=95°C, Sum of two devices

*** Half sine wave 10msec

Electrical Characteristics (Ta = 25°C) *

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	0.55	V	I_F = 4.0 A
Reverse current	I_R	—	—	1.0	mA	V_R = 40 V

* Per one device

HRW26F

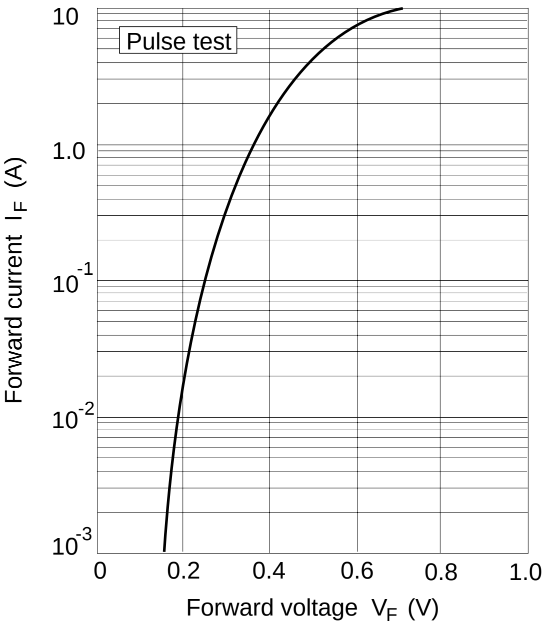


Fig.1 Forward current Vs. Forward voltage

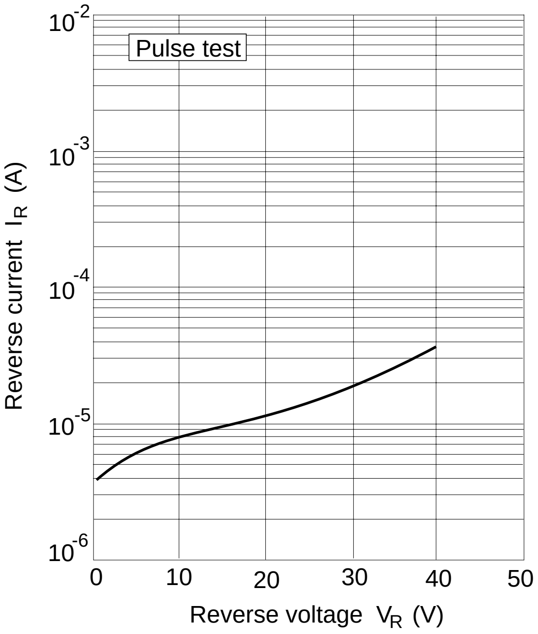
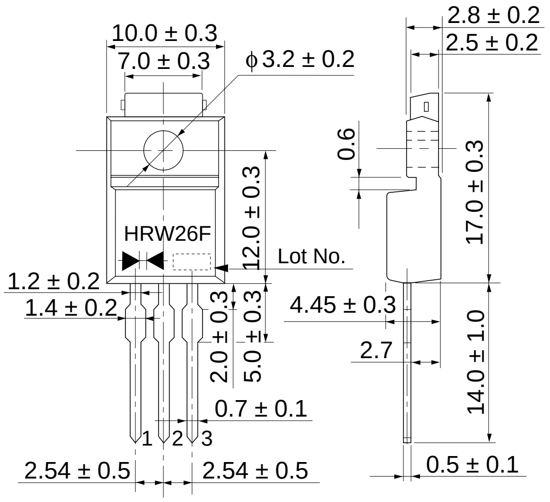


Fig.2 Reverse current Vs. Reverse voltage

Package Dimensions

Unit: mm



1 Anode
2 Cathode
3 Anode

HITACHI Code	TO-220FM
JEDEC Code	—
EIAJ Code	—
Weight (g)	1.8